SamHop Microelectronics Corp.

STU03L01
STD03L01

Ver 1.0

N-Channel Logic Level Enhancement Mode Field Effect Transistor

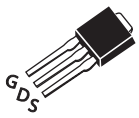
PRODUCT SUMMARY		
V_{DSS}	I_D	$R_{DS(ON)}$ (Ω) Max
100V	2A	0.9 @ VGS=10V
		1.1 @ VGS=4.5V

FEATURES

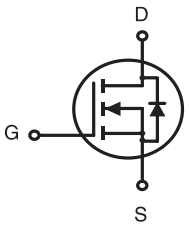
- Super high dense cell design for low $R_{DS(ON)}$.
- Rugged and reliable.
- TO-252 and TO-251 Package.
- ESD Protected.



STU SERIES
TO-252AA(D-PAK)



STD SERIES
TO-251(I-PAK)



ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)

Symbol	Parameter		Limit	Units
V_{DS}	Drain-Source Voltage		100	V
V_{GS}	Gate-Source Voltage		±20	V
I_D	Drain Current-Continuous [a d]	T_C=25°C	2	A
		T_C=70°C	1.6	A
I_{DM}	-Pulsed [b]		5.8	A
P_D	Maximum Power Dissipation	T_C=25°C	42	W
		T_C=70°C	27	W
T_J, T_{STG}	Operating Junction and Storage Temperature Range		-55 to 150	°C

THERMAL CHARACTERISTICS

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	50	°C/W

ELECTRICAL CHARACTERISTICS (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	100			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V , V_{GS}=0V			1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±20V , V_{DS}=0V			±10	uA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} , I_D=250uA	1	2	3	V
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V , I_D=1A		0.72	0.9	ohm
		V_{GS}=4.5V , I_D=0.9A		0.81	1.1	ohm
g_{FS}	Forward Transconductance	V_{DS}=10V , I_D=1A		3.5		S
DYNAMIC CHARACTERISTICS [c]						
C_{ISS}	Input Capacitance	V_{DS}=25V,V_{GS}=0V f=1.0MHz		200		pF
C_{OSS}	Output Capacitance			28		pF
C_{RSS}	Reverse Transfer Capacitance			17		pF
SWITCHING CHARACTERISTICS [c]						
$t_{D(ON)}$	Turn-On Delay Time	V_{DD}=50V I_D=1A V_{GS}=10V R_{GEN}= 6 ohm		20		ns
t_r	Rise Time			19.5		ns
$t_{D(OFF)}$	Turn-Off Delay Time			178		ns
t_f	Fall Time			46		ns
Q_g	Total Gate Charge	V_{DS}=50V,I_D=1A,V_{GS}=10V		4		nC
Q_{gs}	Gate-Source Charge	V_{DS}=50V,I_D=1A, V_{GS}=10V		1		nC
Q_{gd}	Gate-Drain Charge			1.4		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V_{SD}	Diode Forward Voltage	V_{GS}=0V,I_S=1A		0.88	1.3	V

Notes

a.Surface Mounted on FR4 Board,t ≤ 10sec.
b.Pulse Test:Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
c.Guaranteed by design, not subject to production testing.
d.Drain current limited by maximum junction temperature.

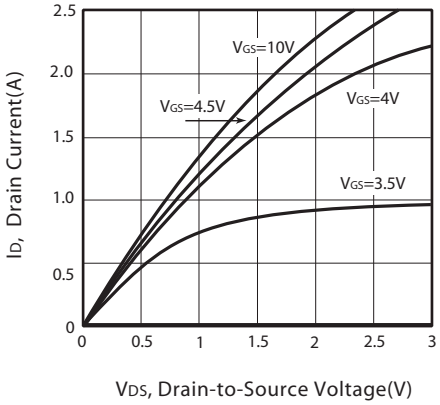


Figure 1. Output Characteristics

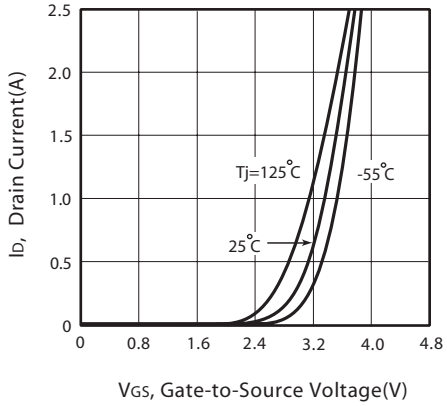


Figure 2. Transfer Characteristics

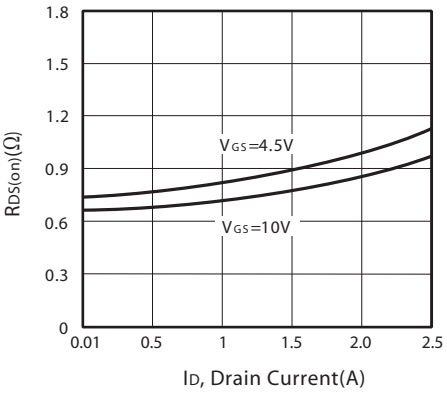


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

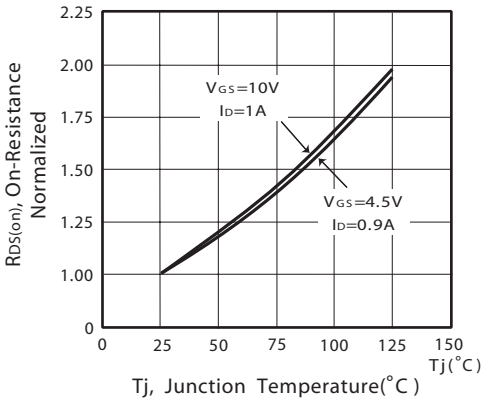


Figure 4. On-Resistance Variation with Drain Current and Temperature

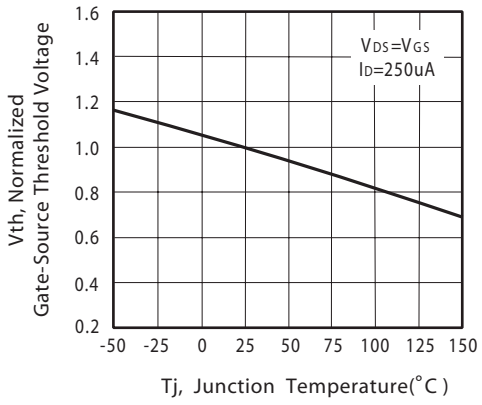


Figure 5. Gate Threshold Variation with Temperature

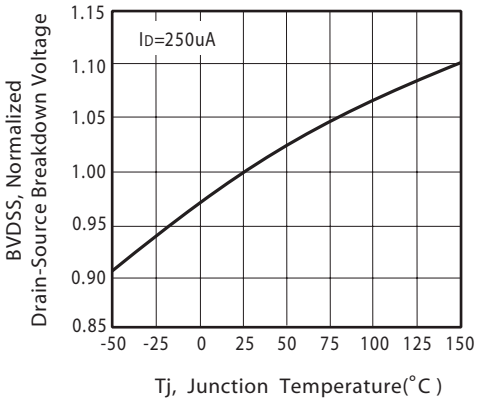


Figure 6. Breakdown Voltage Variation with Temperature

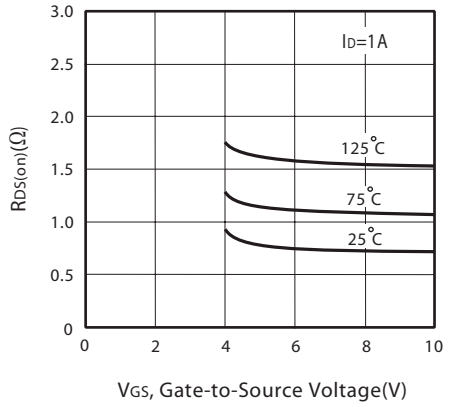


Figure 7. On-Resistance vs. Gate-Source Voltage

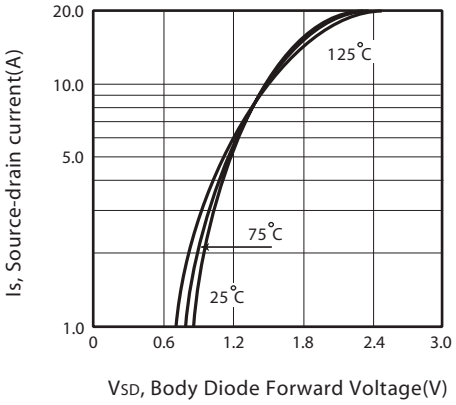


Figure 8. Body Diode Forward Voltage Variation with Source Current

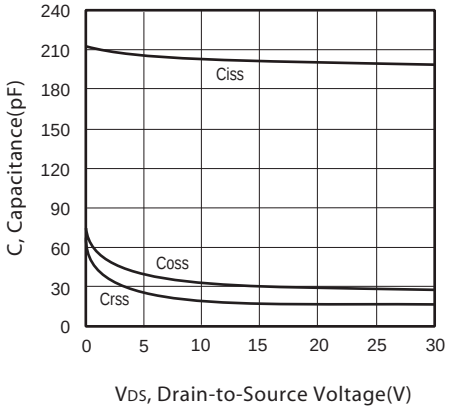


Figure 9. Capacitance

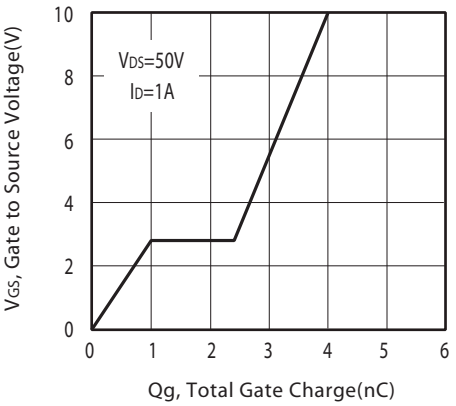


Figure 10. Gate Charge

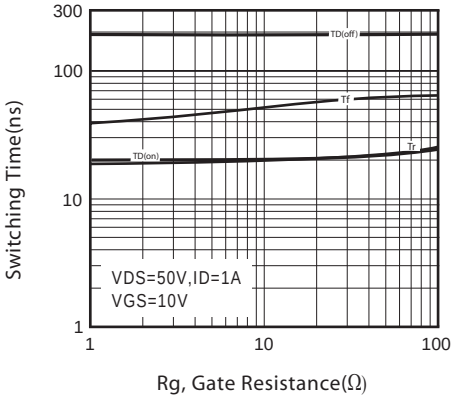


Figure 11. switching characteristics

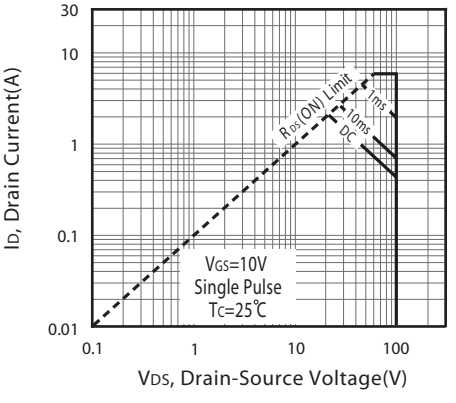


Figure 12. Maximum Safe Operating Area

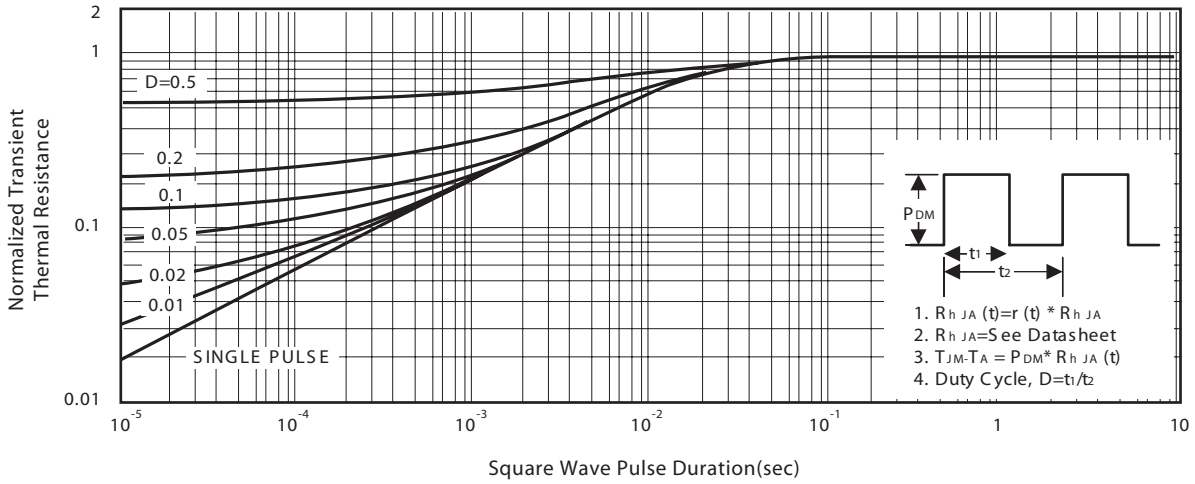
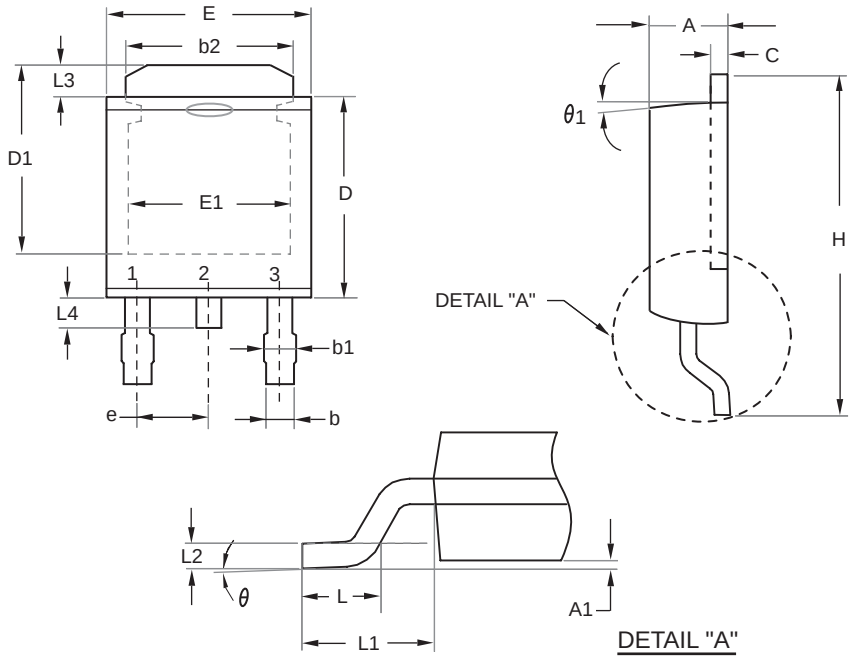


Figure 13. Normalized Thermal Transient Impedance Curve

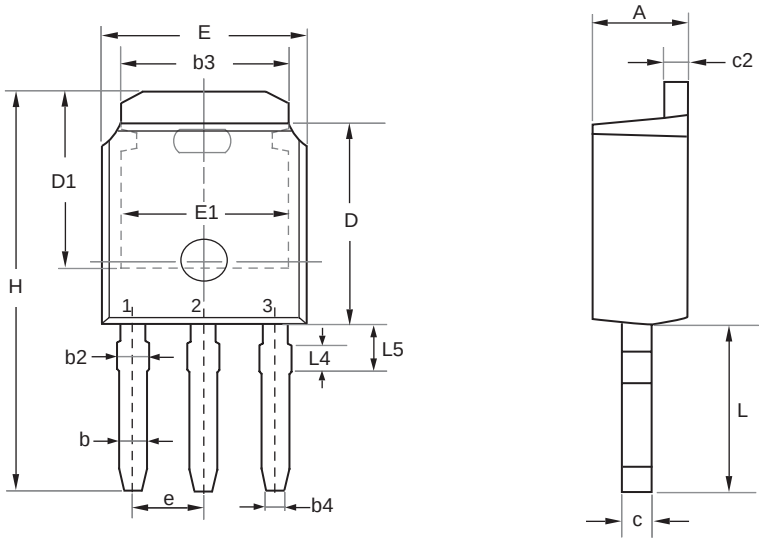
TO-252



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.000	0.200	0.000	0.008
b	0.400	0.889	0.016	0.035
b1	0.770	1.140	0.030	0.045
b2	4.800	5.460	0.189	0.215
C	0.400	0.600	0.016	0.024
D	5.300	6.223	0.209	0.245
D1	4.900	5.515	0.193	0.217
E	6.300	6.731	0.248	0.265
E1	4.400	5.004	0.173	0.197
e	2.290 REF		0.090 BSC	
H	8.900	10.400	0.350	0.409
L	1.397	1.770	0.055	0.070
L1	2.743 REF.		0.108 REF.	
L2	0.508 REF.		0.020 REF.	
L3	0.890	1.700	0.035	0.067
L4	0.500	1.100	0.020	0.043
θ	0°	10°	0°	10°
θ1	7° REF.		7° REF.	

PACKAGE OUTLINE DIMENSIONS

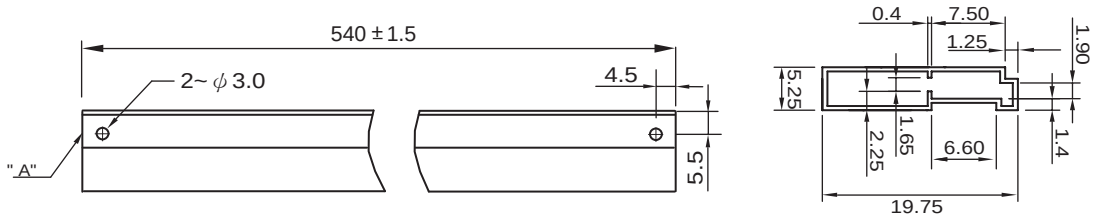
TO-251



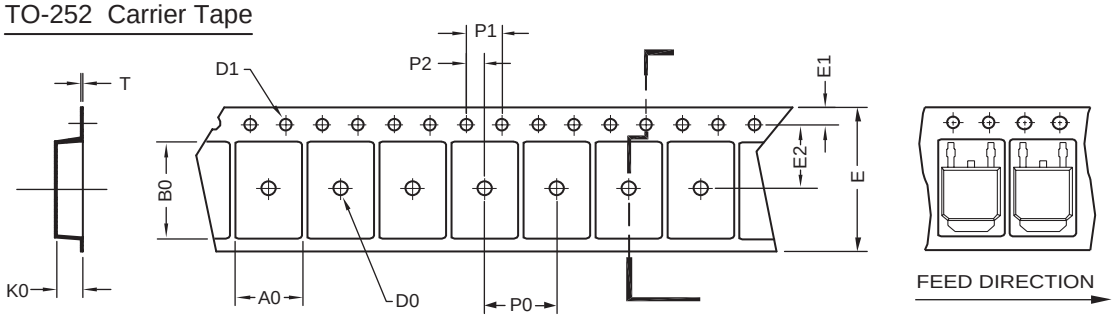
SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
E	6.400	6.731	0.252	0.265
L	3.980	4.280	0.157	0.169
L4	0.698 REF		0.027 REF	
L5	0.972	1.226	0.038	0.048
D	6.000	6.223	0.236	0.245
H	11.050	11.450	0.435	0.450
b	0.640	0.880	0.025	0.035
b2	0.770	1.140	0.030	0.045
b3	5.210	5.460	0.205	0.215
b4	0.450	0.550	0.018	0.022
e	2.286 BSC		0.090 BSC	
A	2.200	2.380	0.087	0.094
c	0.400	0.600	0.016	0.024
c2	0.400	0.600	0.016	0.024
D1	5.100	---	0.201	---
E1	4.400	---	0.173	---

TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



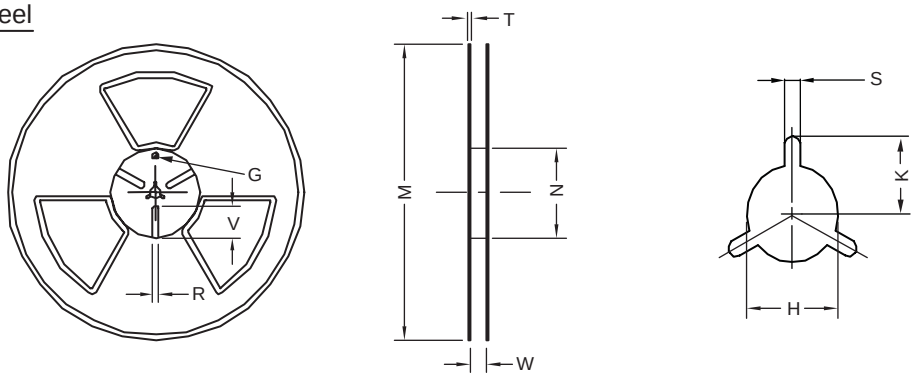
TO-252 Carrier Tape



UNIT:㎜

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 ㎜)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	ϕ 2	ϕ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel

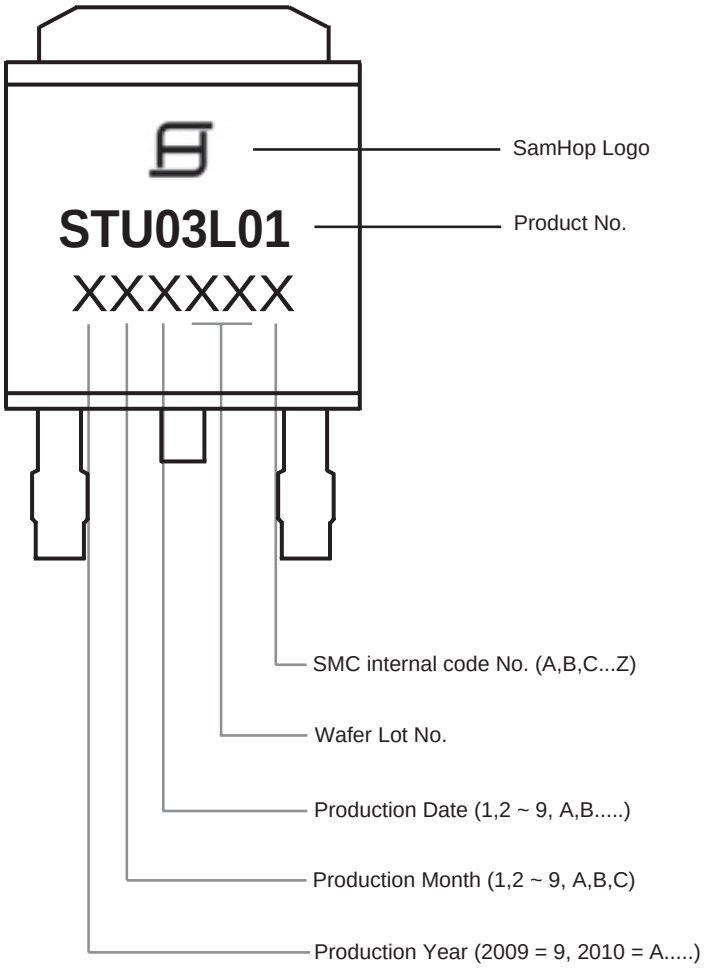


UNIT:㎜

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 ㎜	ϕ 330	ϕ 330 ± 0.5	ϕ 97 ± 1.0	17.0 + 1.5 - 0	2.2	ϕ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---

TOP MARKING DEFINITION

TO-252



TOP MARKING DEFINITION

TO-251

